

4.980x3.820mm Silicon Finger PIN PD Chip datasheet

P/N : WS81-01C

Feature

Si PIN photodiode chip

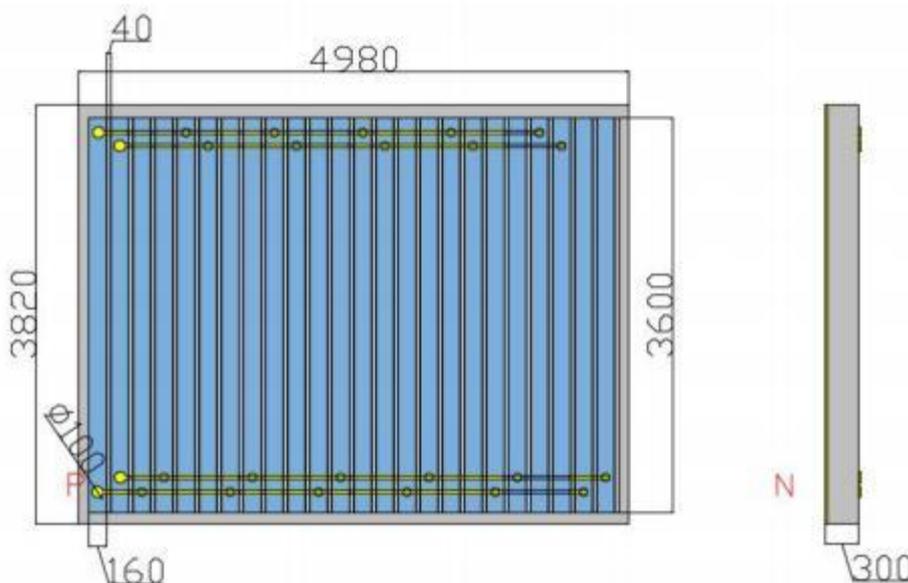
Structure

Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au

Top side (Anode) : Al



DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	160 X 3600 X 24(pcs)			μm
Chip width	3820 ± 30			μm
Chip length	4980 ± 30			μm
Chip height	275	300	325	μm
Pad Area	90	100	110	μm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Reverse Dark Current	Id	Vr=10V				nA
Sensitive Wavelength Range	λ					nm
Capacitance	Cj	VR=5V, f=1MHz				pF